September 2001

FDC634P

# P-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

### **General Description**

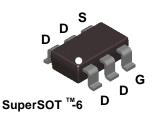
This P-Channel 2.5V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

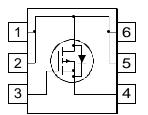
### Applications

- Battery management
- · Load switch
- Battery protection

## Features

- -3.5 A, -20 V.  $R_{DS(ON)} = 80 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$  $R_{DS(ON)} = 110 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
- Low gate charge (7.2 nC typical)
- High performance trench technology for extremely low R<sub>DS(ON)</sub>





# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

| Symbol           | Parameter                               |            | Ratings     | Units |
|------------------|---|------------|-------------|-------|
| V <sub>DSS</sub> | Drain-Source Voltage                    |            | -20         | V     |
| V <sub>GSS</sub> | Gate-Source Voltage                     |            | ±8          | V     |
| l <sub>D</sub>   | Drain Current – Continuous              | (Note 1a)  | -3.5        | A     |
|                  | - Pulsed                                |            | -20         |       |
| PD               | Maximum Power Dissipation               | (Note 1a)  | 1.6         | W     |
|                  |   | (Note 1b)  | 0.8         |       |
| $T_J, T_{STG}$   | Operating and Storage Junction Temperat | ture Range | -55 to +150 | °C    |

# Thermal Characteristics

| $R_{\theta JA}$  | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 78 | °C/W |
|------------------|---|-----------|----|------|
| R <sub>θJC</sub> | Thermal Resistance, Junction-to-Case    | (Note 1)  | 30 | °C/W |

# **Package Marking and Ordering Information**

| Device Marking | Device  | Reel Size | Tape width | Quantity   |
|----------------|---------|-----------|------------|------------|
| .634           | FDC634P | 7"        | 8mm        | 3000 units |

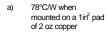
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FDC634P

| Symbol                               | Parameter   | Test Conditions   | Min  | Тур            | Max              | Units |
|--------------------------------------|---|---|------|----------------|------------------|-------|
| Off Char                             | acteristics                                       |   |      |                |                  |       |
| BV <sub>DSS</sub>                    | Drain–Source Breakdown Voltage                    | $V_{GS} = 0 V, I_D = -250 \mu A$  | -20  |                |                  | V     |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature<br>Coefficient      | $I_D = -250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$   |      | -12            |                  | mV/⁰C |
| DSS                                  | Zero Gate Voltage Drain Current                   | $V_{DS} = -16 V$ , $V_{GS} = 0 V$   |      |                | -1               | μA    |
| GSSF                                 | Gate-Body Leakage, Forward                        | $V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$   |      |                | 100              | nA    |
| GSSR                                 | Gate-Body Leakage, Reverse                        | $V_{GS} = -8 V$ $V_{DS} = 0 V$  |      |                | -100             | nA    |
| On Char                              | acteristics (Note 2)                              |   |      |                |                  |       |
| V <sub>GS(th)</sub>                  | Gate Threshold Voltage                            | $V_{DS} = V_{GS}, I_D = -250 \ \mu A$   | -0.4 | -0.8           | -1.5             | V     |
| <u>ΔVgs(th)</u><br>ΔTj               | Gate Threshold Voltage<br>Temperature Coefficient | $I_D = -250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$   |      | 3              |                  | mV/ºC |
| R <sub>DS(on)</sub>                  | Static Drain–Source<br>On–Resistance              | $ \begin{array}{l} V_{GS} = -4.5 \ V,  b_{D} = -3.5 \ A \\ V_{GS} = -2.5 \ V,  b_{D} = -3.1 \ A \\ V_{GS} = -4.5 \ V, \ b_{D} = -3.5 A, T_{J} = 125^{\circ} C \end{array} $ |      | 60<br>82<br>77 | 80<br>110<br>130 | mΩ    |
| D(on)                                | On–State Drain Current                            | $V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$   | -10  |                |                  | А     |
| <b>g</b> fs                          | Forward Transconductance                          | $V_{DS} = -5 V$ , $I_D = -3.5 A$  |      | 11             |                  | S     |
| Dvnamic                              | Characteristics                                   |   |      |                |                  |       |
| Ciss                                 | Input Capacitance                                 | $V_{DS} = -10 V$ , $V_{GS} = 0 V$ ,   |      | 779            |                  | pF    |
| Coss                                 | Output Capacitance                                | f = 1.0 MHz   |      | 121            |                  | pF    |
| C <sub>rss</sub>                     | Reverse Transfer Capacitance                      |   |      | 56             |                  | pF    |
| Switchin                             | g Characteristics (Note 2)                        | •   |      |                |                  |       |
| t <sub>d(on)</sub>                   | Turn–On Delay Time                                | $V_{DD} = -10 V$ , $I_D = -1 A$ ,   |      | 10             | 20               | ns    |
| tr                                   | Turn–On Rise Time                                 | $V_{GS} = -4.5 \ V, \qquad R_{GEN} = 6 \ \Omega$  |      | 9              | 19               | ns    |
| t <sub>d(off)</sub>                  | Turn–Off Delay Time                               |   |      | 27             | 43               | ns    |
| t <sub>f</sub>                       | Turn–Off Fall Time                                |   |      | 11             | 20               | ns    |
| Qg                                   | Total Gate Charge                                 | $V_{DS} = -10 V$ , $I_D = -3.5 A$ ,   |      | 7.2            | 10               | nC    |
| Q <sub>gs</sub>                      | Gate-Source Charge                                | $V_{GS} = -4.5 V$   |      | 1.7            |                  | nC    |
| Q <sub>gd</sub>                      | Gate–Drain Charge                                 |   |      | 1.5            |                  | nC    |
| Drain–So                             | ource Diode Characteristics                       | and Maximum Ratings   |      |                |                  |       |
| Is                                   | Maximum Continuous Drain-Source                   | 0   |      |                | -1.3             | Α     |
| V <sub>SD</sub>                      | Drain–Source Diode Forward<br>Voltage             | $V_{GS} = 0 V$ , $I_S = -1.3 A$ (Note 2)  |      | -0.8           | -1.2             | V     |

the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.





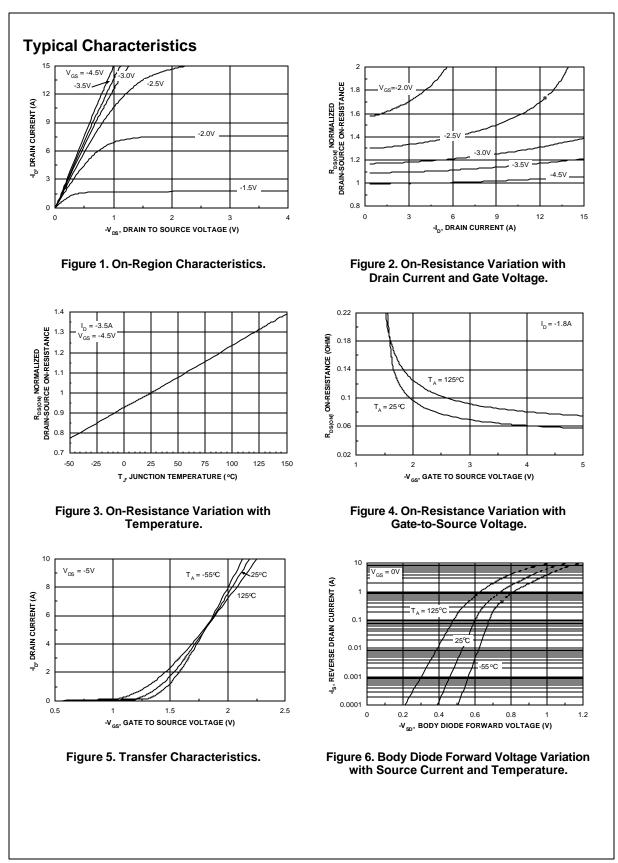


b) 156°C/W when mounted on a minimum pad of 2 oz copper

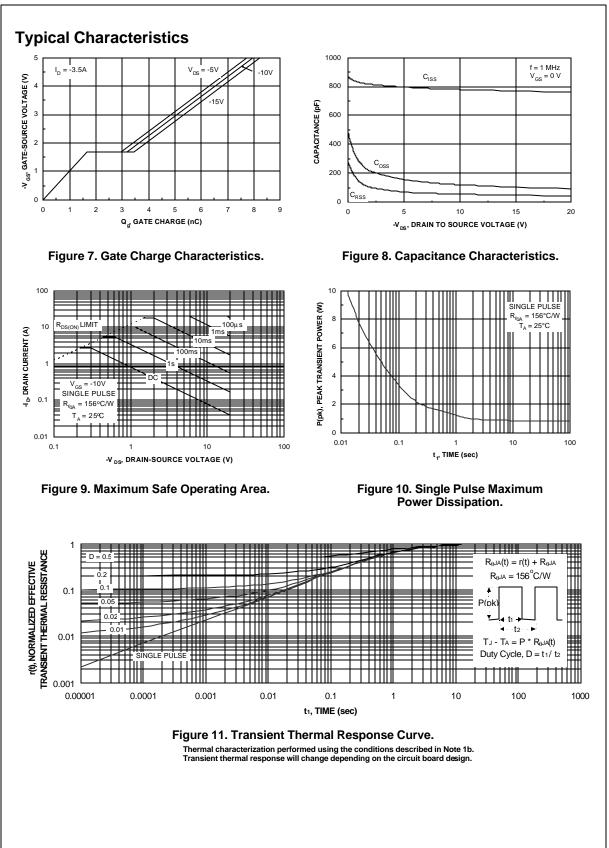
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu s,$  Duty Cycle < 2.0%

FDC634P Rev E(W)



FDC634P



FDC634P

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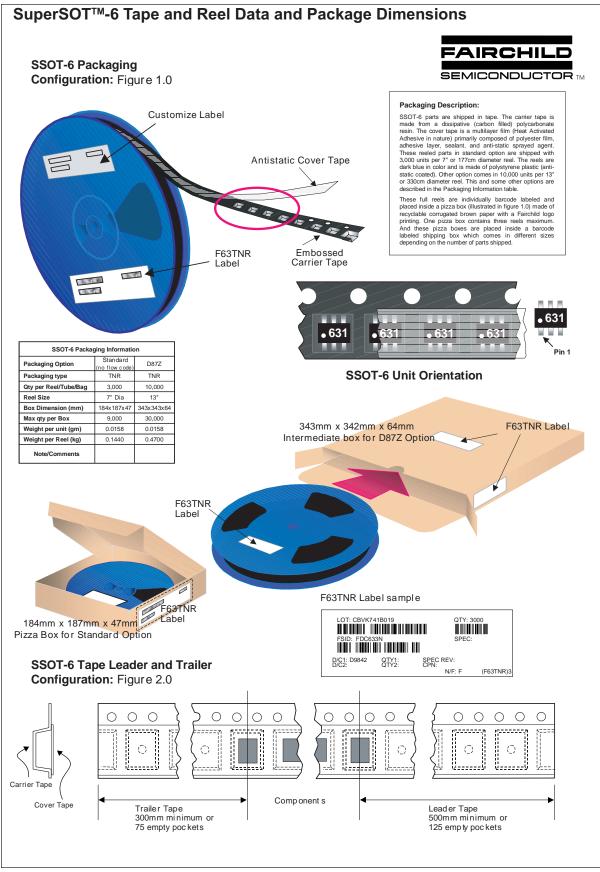
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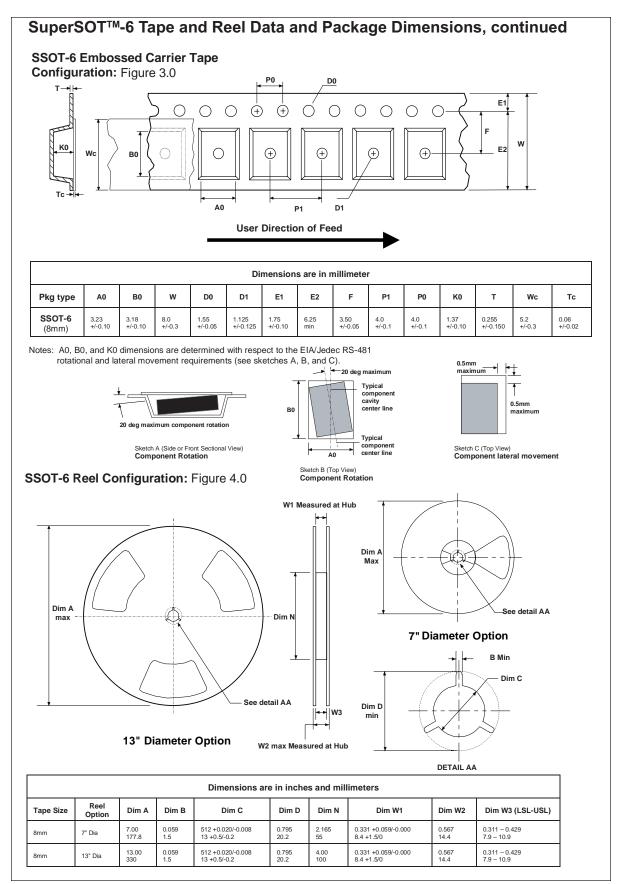
#### **PRODUCT STATUS DEFINITIONS**

**Definition of Terms** 

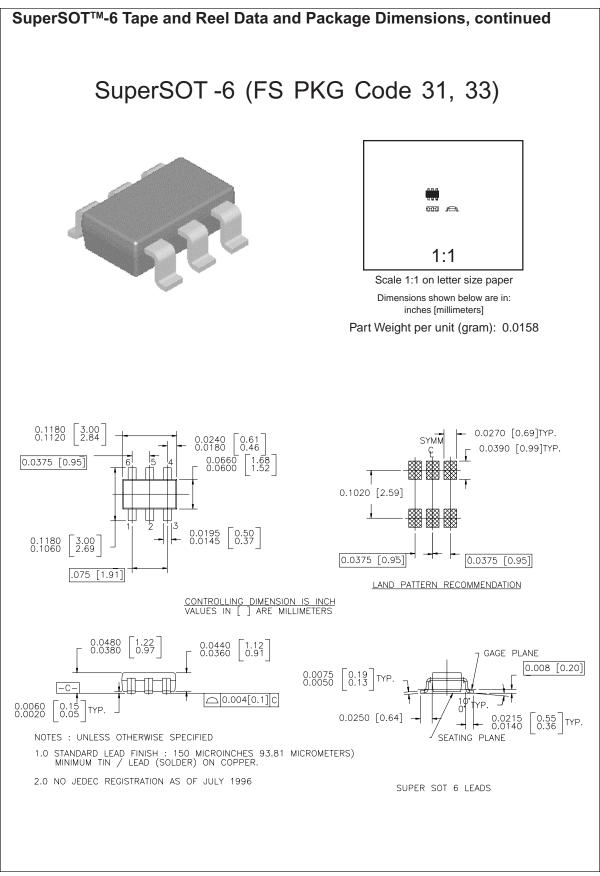
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August 1999, Rev. C



July 1999, Rev. C



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